

30 V, 3 A PNP low VCEsat (BISS) transistor

11 September 2014

Product data sheet

### 1. General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

NPN complement: PBSS4330PAS

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  ${\sf I}_C$  and  ${\sf I}_{CM}$
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1.     Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-30	V
I <sub>C</sub>	collector current			-	-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-5	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	75	107	mΩ



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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	E	emitter		1-1
3	С	collector	1   2   Transparent top view	2 sym013
			DFN2020D-3 (SOT1061D)	

## 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS5330PAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body $2 \times 2 \times 0.65$ mm	SOT1061D			

### 7. Marking

Table 4.   Marking codes	
Type number	Marking code
PBSS5330PAS	E2

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### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	А
I <sub>B</sub>	base current			-	-500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	600	mW
			[2][3]	-	1.2	W
			[4]	-	1.5	W
			[5][6]	-	2.5	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

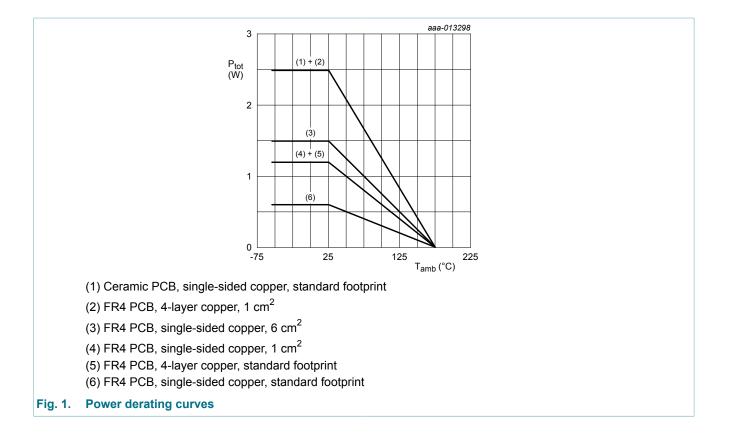
[3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

[6] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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### 9. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	-	250	K/W
		[2][3]	-	-	125	K/W	
	ambient		[4]	-	-	100	K/W
			[5][6]	-	-	60	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

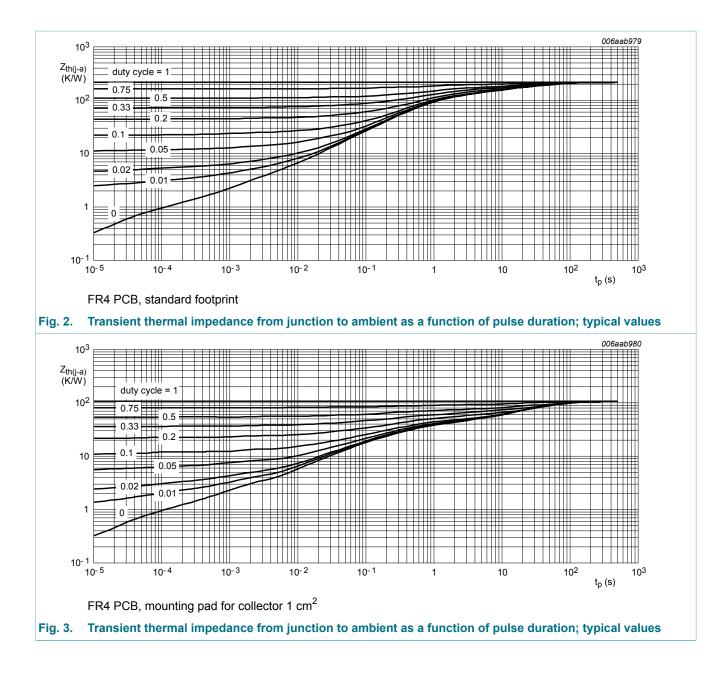
[3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

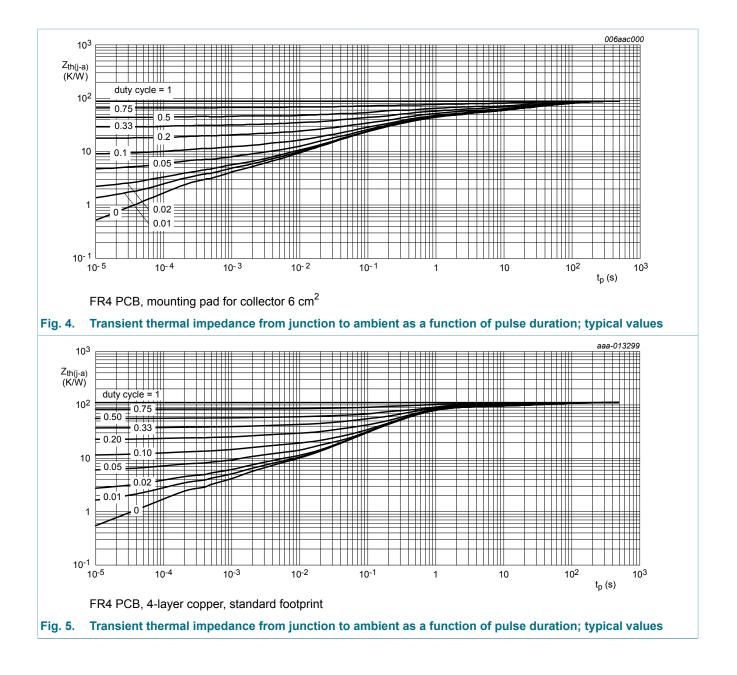
[5] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

<sup>[6]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

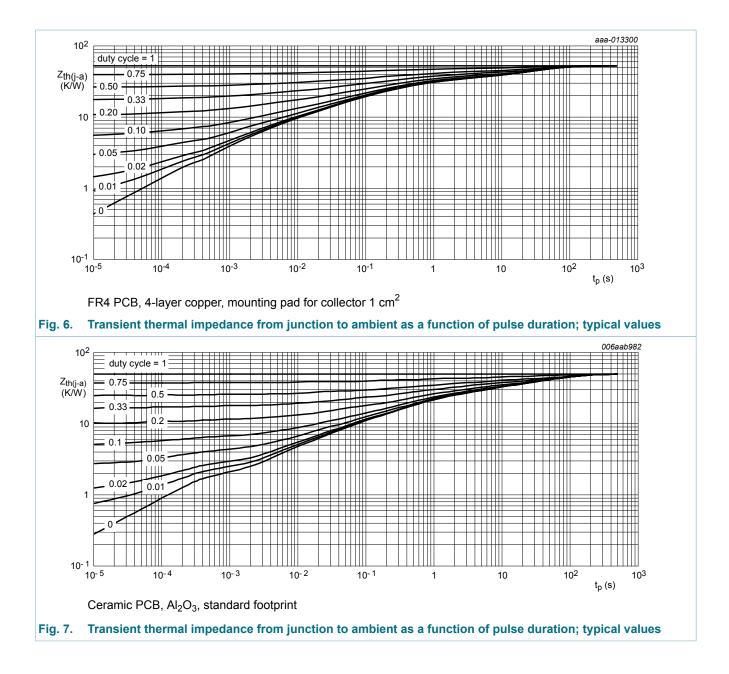












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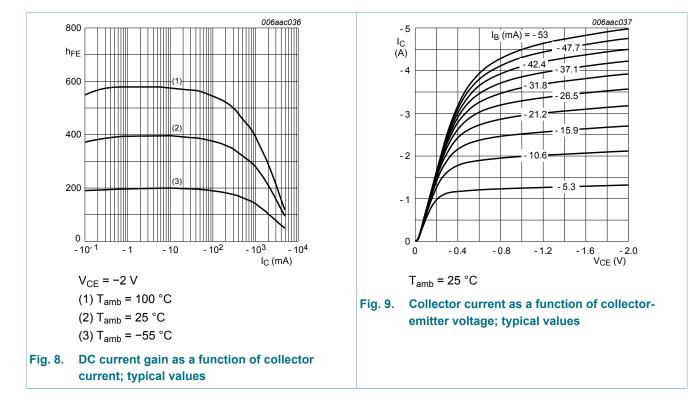
### **10. Characteristics**

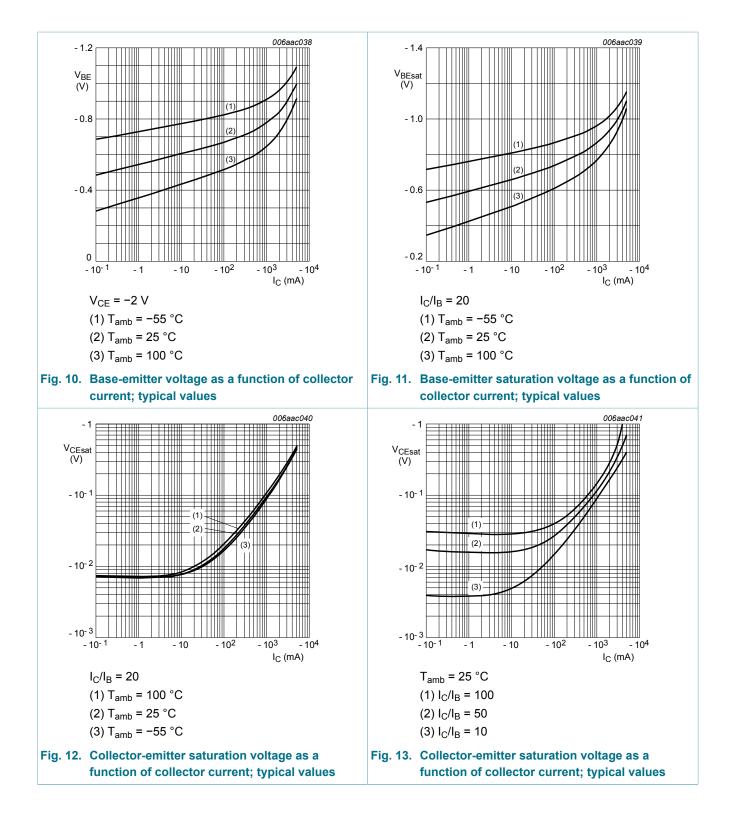
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -24 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -0.5 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	320	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	175	280	450	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -2 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	140	210	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -3 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	100	160	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -0.5 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-45	-70	mV
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-90	-130	mV
		$I_{C}$ = -2 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-170	-240	mV
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed;	-	-230	-320	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^\circ C$	-	75	107	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -2 A; $I_{B}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 µs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.89	-1.1	V
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.97	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-0.75	-1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -9 V; I <sub>C</sub> = -2 A; I <sub>Bon</sub> = -0.1 A;	-	11	-	ns
t <sub>r</sub>	rise time	$I_{Boff}$ = 0.1 A; $T_{amb}$ = 25 °C	-	59	-	ns
on	turn-on time		-	70	-	ns
s	storage time		-	165	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
t <sub>off</sub>	turn-off time	-	-	200	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	165	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	38	45	pF

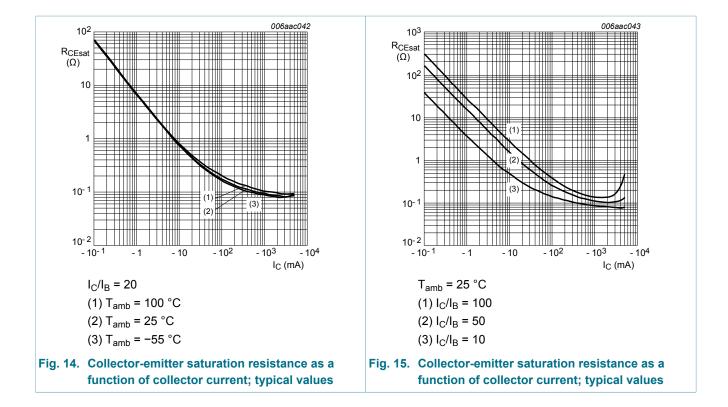




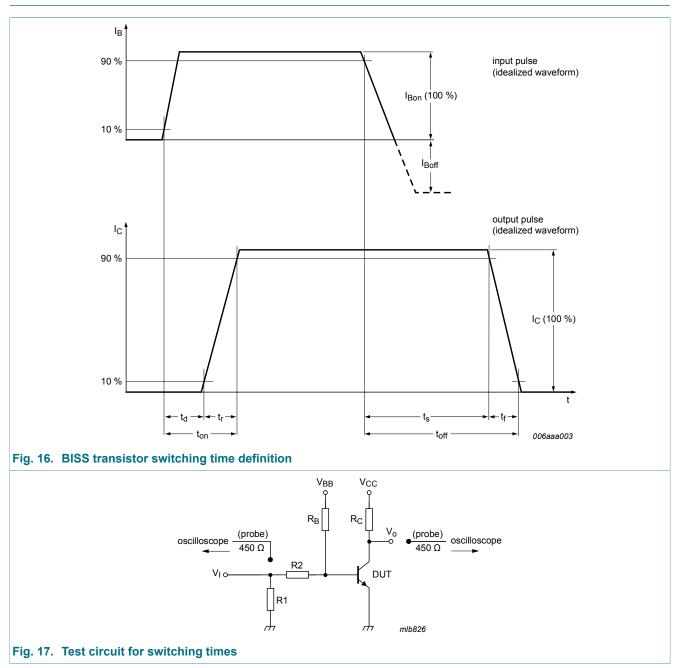
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## PBSS5330PAS

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### **11. Test information**

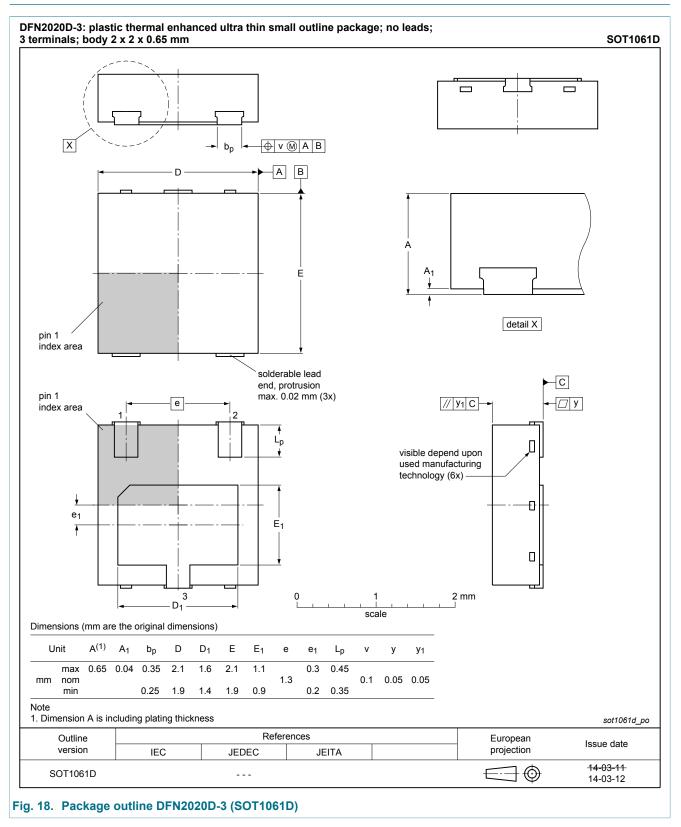
#### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 12. Package outline



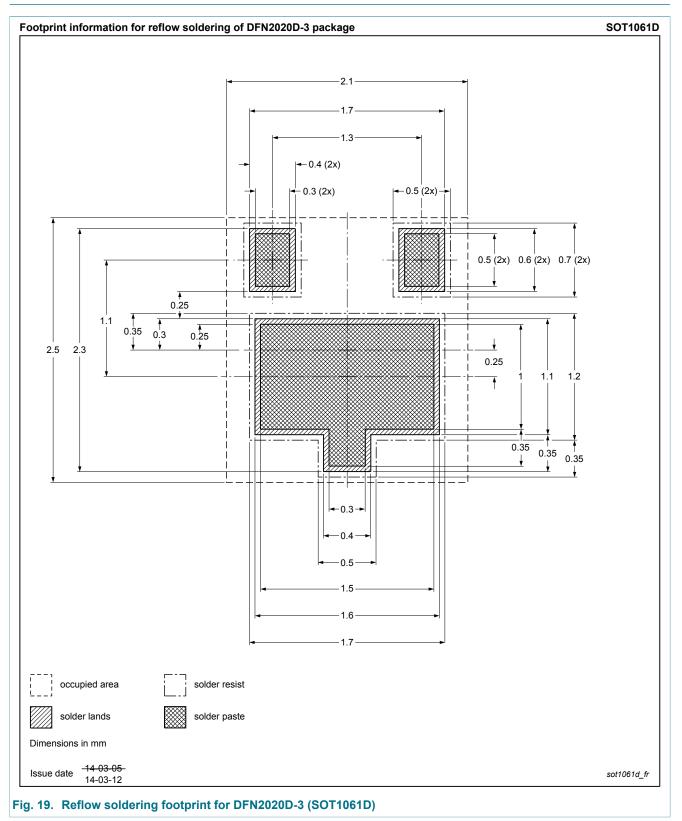
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### 13. Soldering



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## 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5330PAS v.1	20140911	Product data sheet	-	-		

#### 30 V, 3 A PNP low VCEsat (BISS) transistor

### 15. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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